



STB155N3H6 STD155N3H6

N-channel 30 V, 2.5 mΩ, 80 A, D²PAK, DPAK
STripFET™ VI DeepGATE™ Power MOSFET

Features

Order codes	V _{DSS}	R _{DS(on)} max	I _D
STB155N3H6	30 V	< 3 mΩ	80 A ⁽¹⁾
STD155N3H6	30 V	< 3 mΩ	80 A ⁽¹⁾

1. Limited by wire bonding

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- High avalanche ruggedness

Application

- Switching applications
- Automotive

Description

These devices are 30 V N-channel Power MOSFETs realized using ST's proprietary STripFET™ VI technology. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

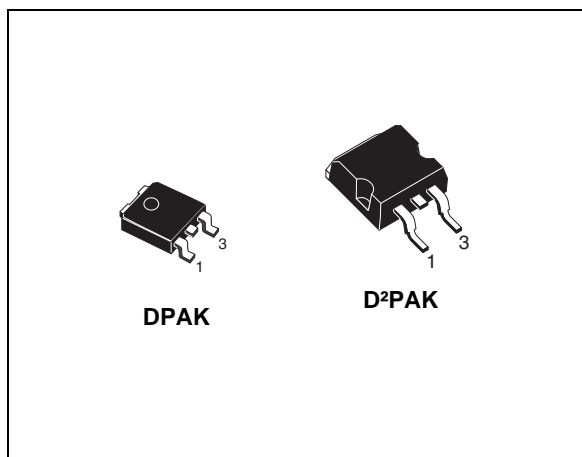
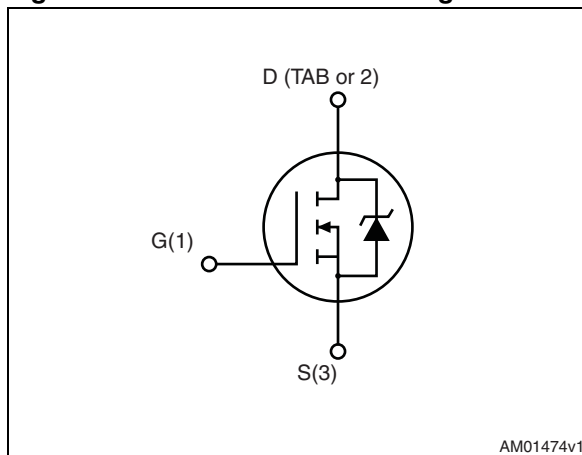


Figure 1. Internal schematic diagram



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Table 1. Device summary

Order codes	Marking	Package	Packaging
STB155N3H6	155N3H6	D ² PAK	Tape and reel
STD155N3H6		DPAK	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
	Derating factor	0.73	W/ $^\circ\text{C}$
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		$^\circ\text{C}$

1. Limited by wire bonding
2. Pulse width limited by safe operating area

Table 3. Thermal resistance

Symbol	Parameter	Value		Unit
		D ² PAK	DPAK	
$R_{thj-case}$	Thermal resistance junction-case max	1.36		$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	35	50	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch² 2 oz Cu board

Table 4. Avalanche characteristics

Symbol	Parameters	Value	Unit
I_{AV}	Not-repetitive avalanche current	40	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 22\text{ V}$)	525	mJ

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 5. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 20\text{ V}$ $V_{DS} = 20\text{ V}$, $T_c = 125\text{ °C}$			1 100	μA nA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$		2.5	3.0	m Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		3650		pF
C_{oss}	Output capacitance		-	765	-	pF
C_{rss}	Reverse transfer capacitance				390	pF
Q_g	Total gate charge	$V_{DD} = 15\text{ V}$, $I_D = 80\text{ A}$		62		nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{ V}$	-	17	-	nC
Q_{gd}	Gate-drain charge	Figure 14		16		nC
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.5	-	Ω

Table 7. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 13)	-	20	-	ns
t_r	Rise time			90		ns
$t_{d(off)}$	Turn-off delay time		-	50	-	ns
t_f	Fall time			20		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 80\text{ A}$, $V_{GS} = 0$	-		1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 24\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 15)	-	40		ns
Q_{rr}	Reverse recovery charge			50		nC
I_{RRM}	Reverse recovery current			2.5		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

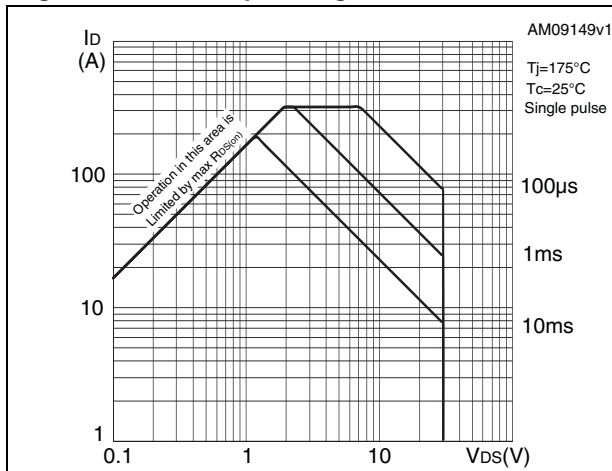


Figure 3. Thermal impedance

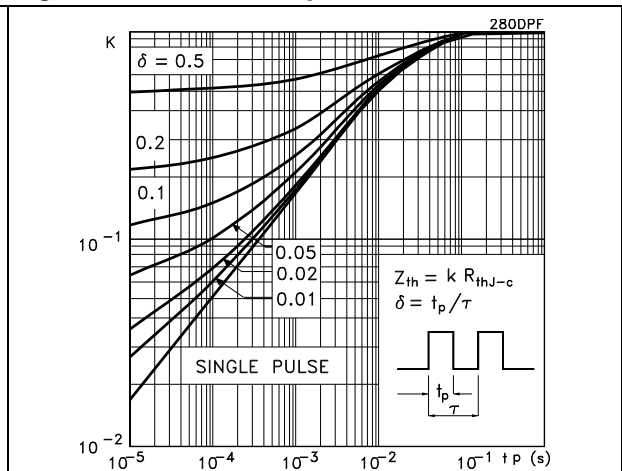


Figure 4. Output characteristics

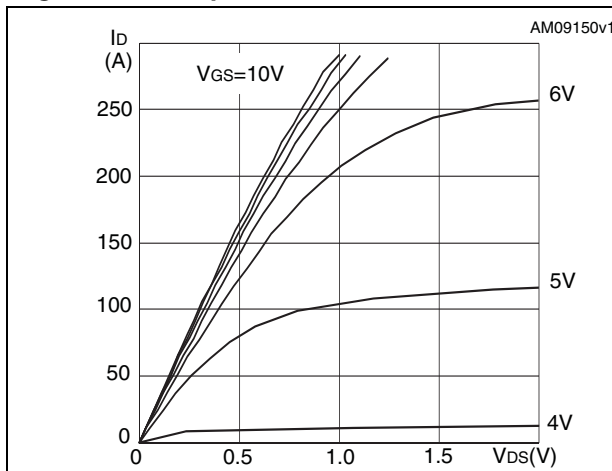


Figure 5. Transfer characteristics

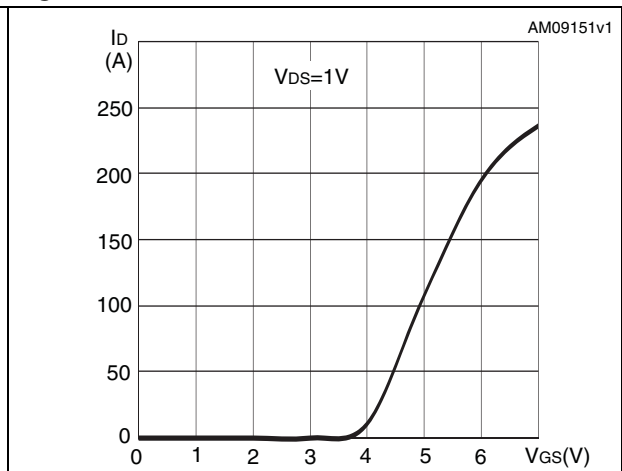


Figure 6. Normalized $B_{V_{DSS}}$ vs temperature

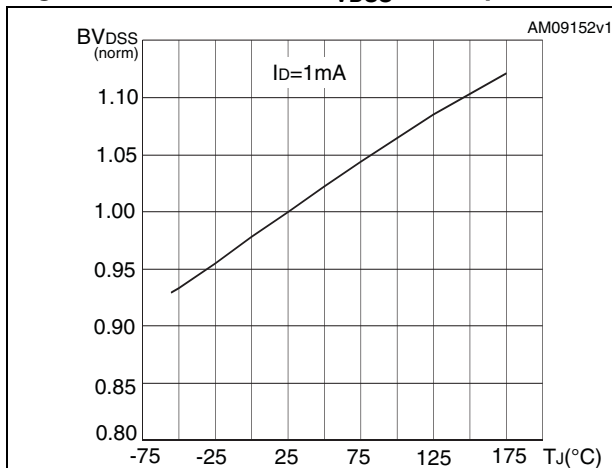


Figure 7. Static drain-source on resistance

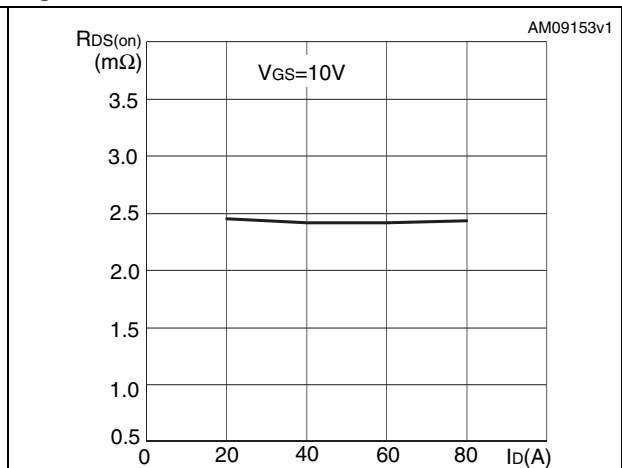


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

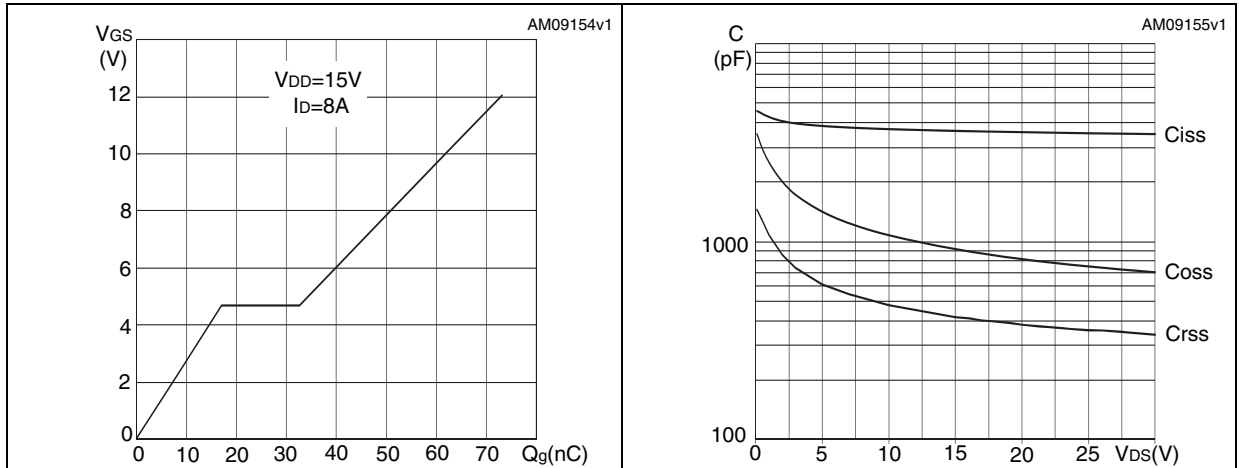


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

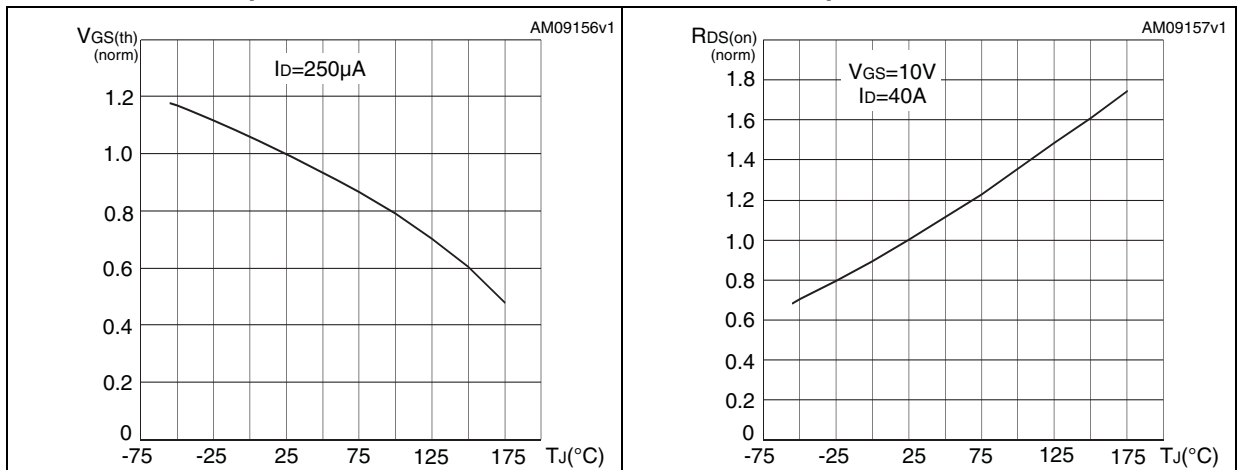
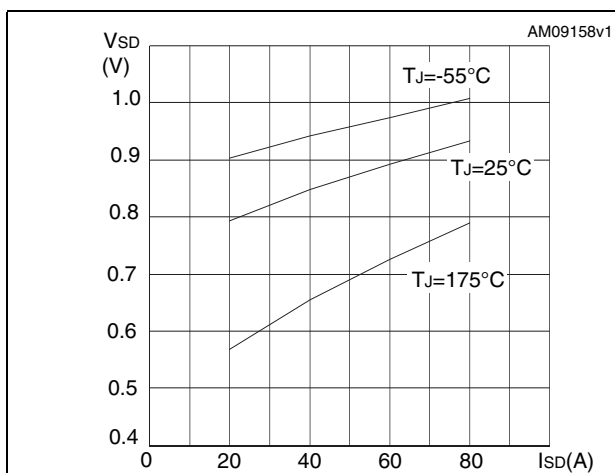
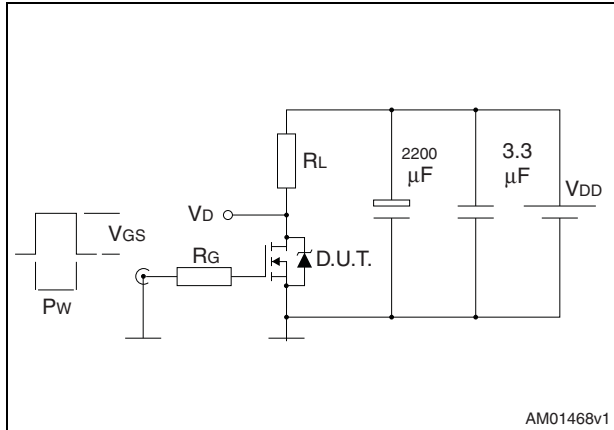


Figure 12. Source-drain diode forward characteristics



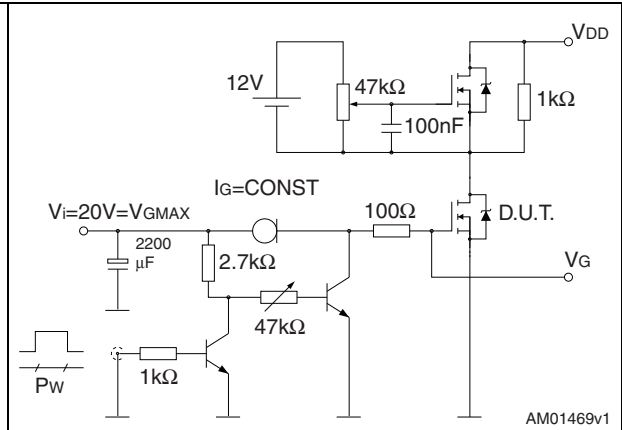
3 Test circuits

Figure 13. Switching times test circuit for resistive load



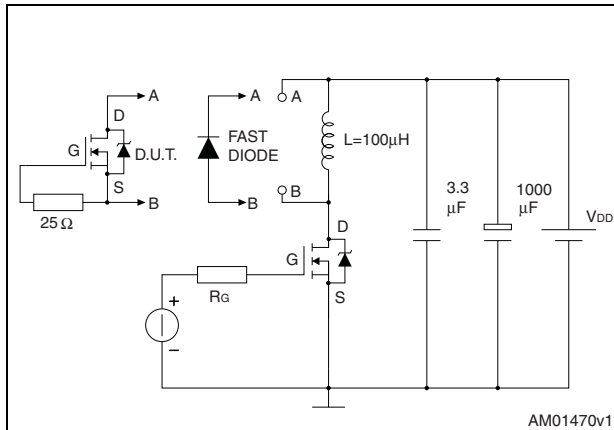
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Figure 14. Gate charge test circuit



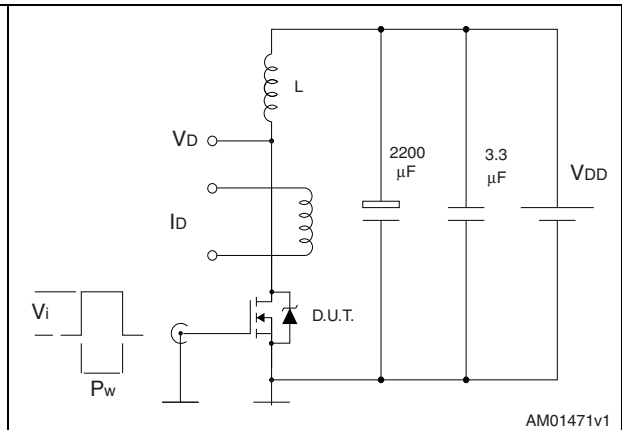
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Figure 15. Test circuit for inductive load switching and diode recovery times



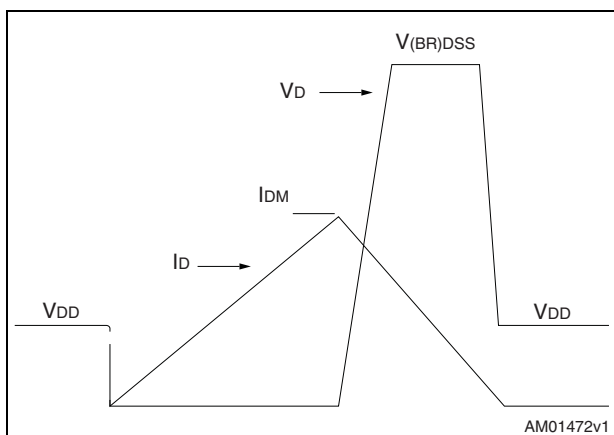
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Figure 16. Unclamped inductive load test circuit



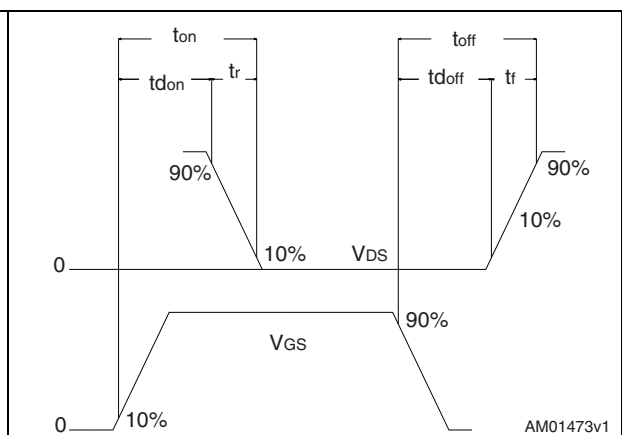
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Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



AM01473v1

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 19. D²PAK footprint^(a)

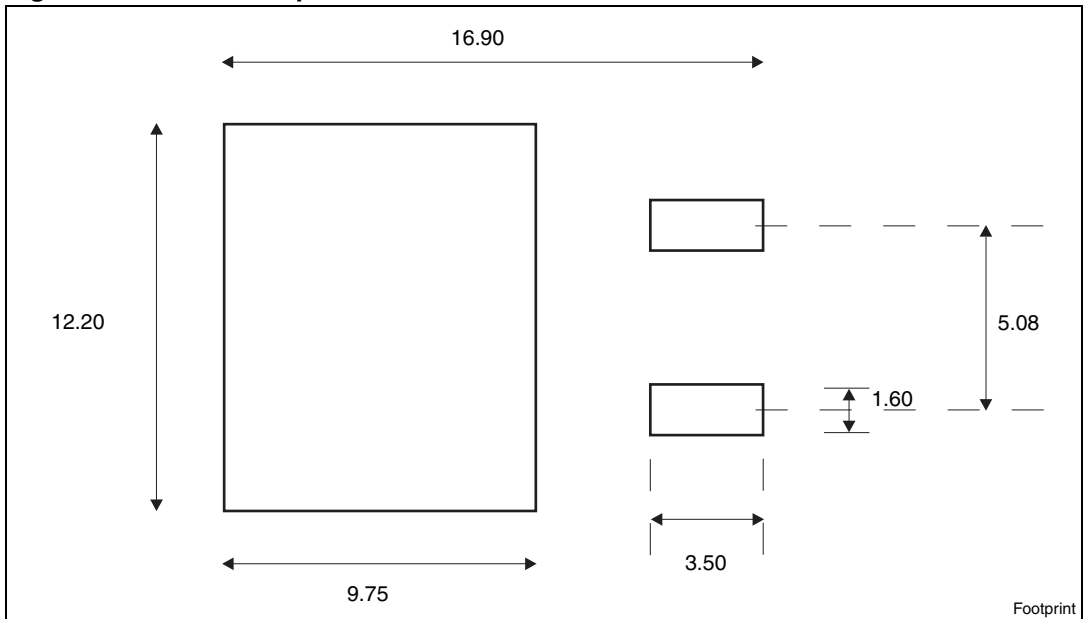
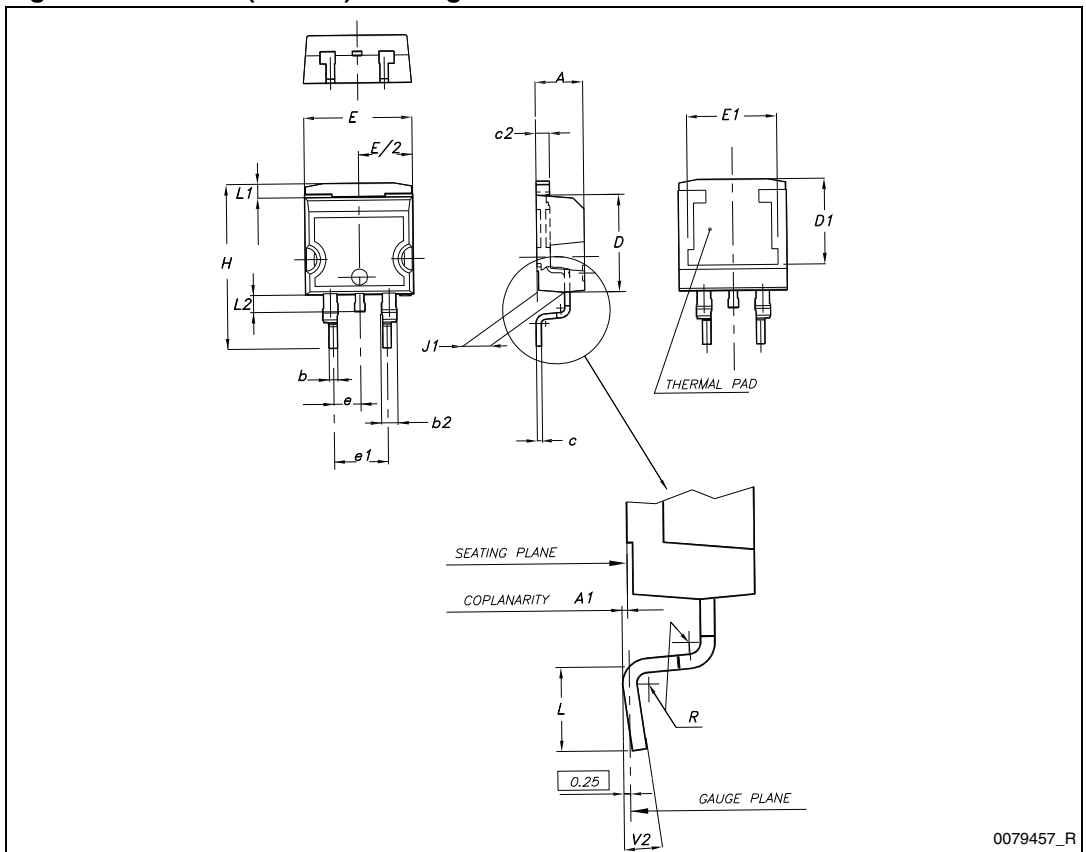


Figure 20. D²PAK (TO-263) drawing

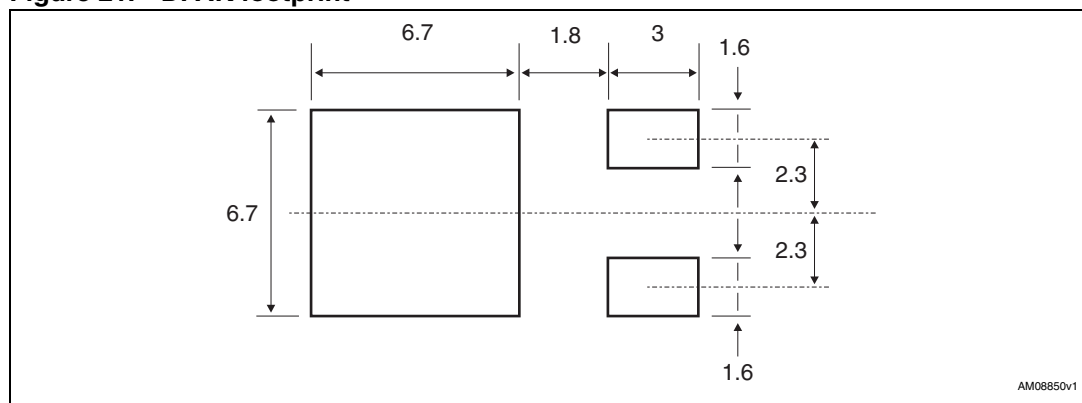


a. All dimension are in millimeters

Table 10. DPAK (TO-252) mechanical data

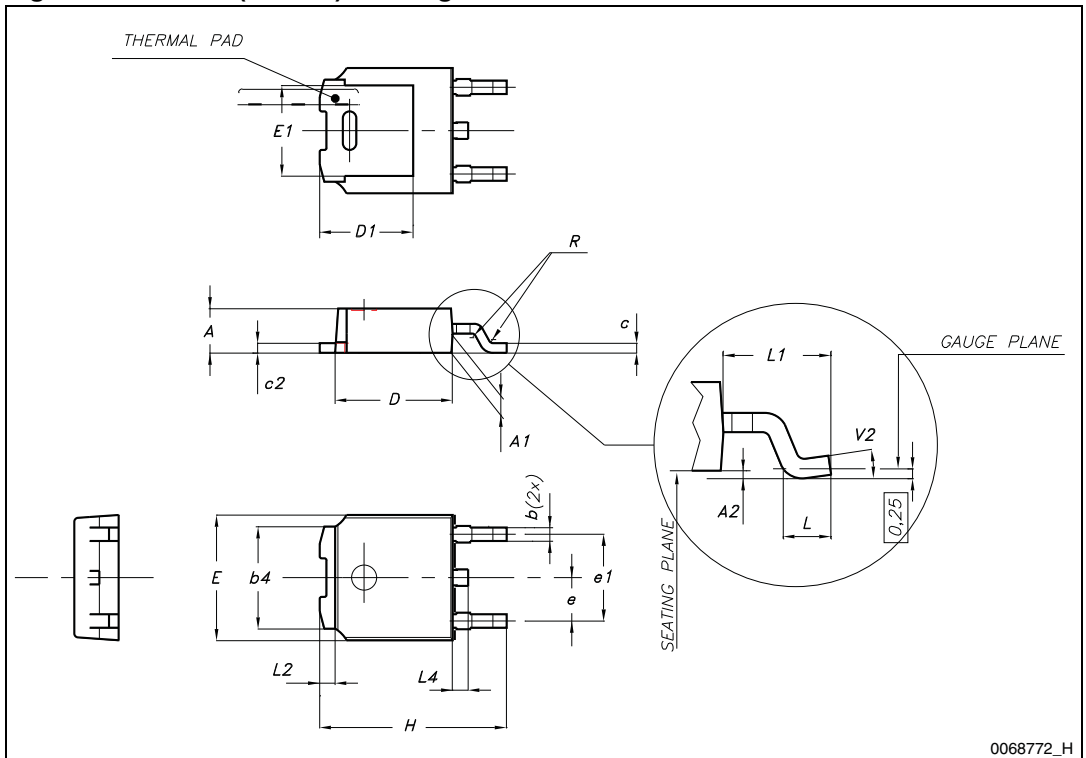
Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		1.50
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 21. DPAK footprint^(b)



b. All dimension are in millimeters

Figure 22. DPAK (TO-252) drawing



5 Packaging mechanical data

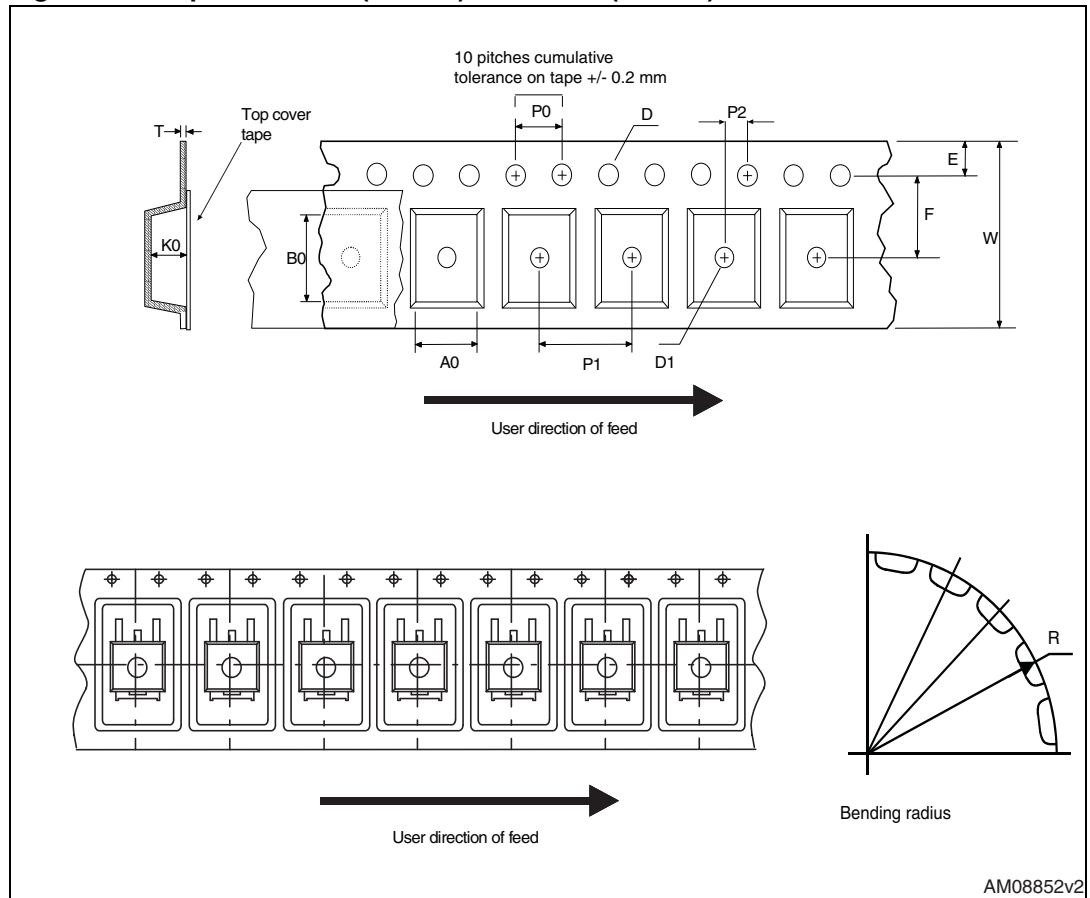
Table 11. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Table 12. DPAK (TO-252) tape and reel mechanical data

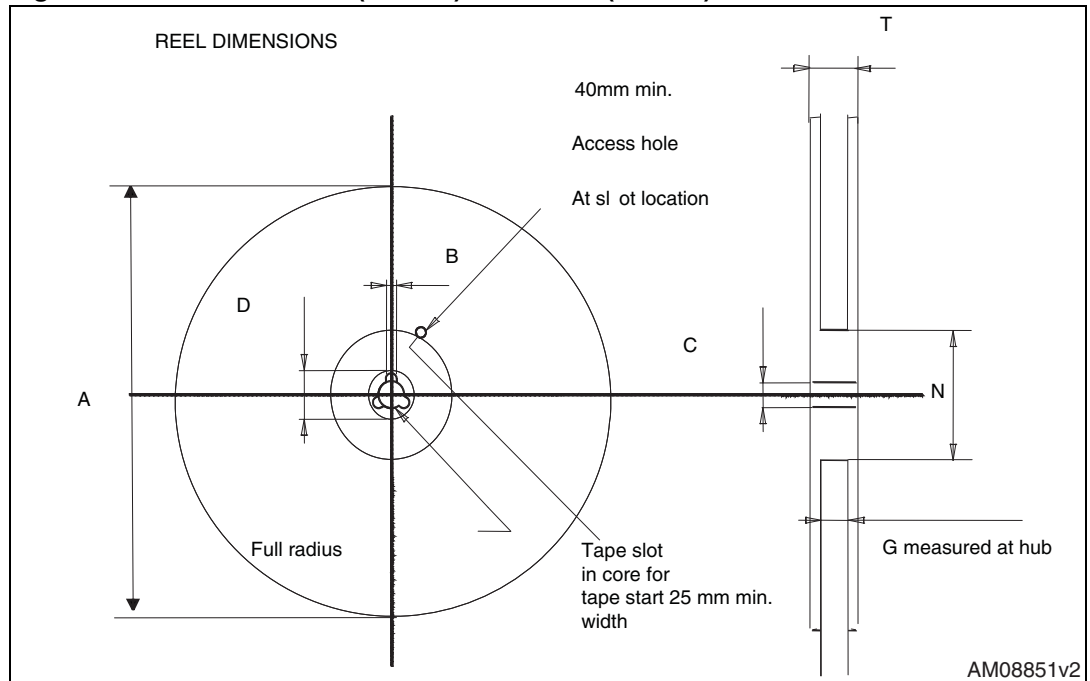
Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 23. Tape for D²PAK (TO-263) and DPAK (TO-252)



AM08852v2

Figure 24. Reel for D²PAK (TO-263) and DPAK (TO-252)



AM08851v2

6 Revision history

Table 13. Document revision history

Date	Revision	Changes
03-May-2011	1	First release.
11-May-2011	2	Document status promoted from preliminary data to datasheet.

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